

WHAT IS CLAIMED IS:—

1. A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a
5 current value flowing in the light emitting element; and

a second transistor provided in said pixel for determining a
light emission or non-emission of the light emitting element according
to a video signal,

wherein the light emitting element is connected in series to
10 the first transistor and the second transistor between a first power
supply and a second power supply;

a gate electrode of the first transistor is connected to the
first power supply; and

the first transistor is a depletion mode transistor.

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2. A device according to claim 1, wherein each of the first
transistor and the second transistor has a P-type conductivity and
a threshold potential of the first transistor is higher than a
threshold potential of the second transistor.

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3. A device according to claim 1, wherein each of the first
transistor and the second transistor has an N-type conductivity and
a threshold potential of the first transistor is lower than a threshold
potential of the second transistor.

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4. A device according to claim 1, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.

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5. A device according to claim 4, a ratio of the channel length to the channel width of the first transistor is five or more.

6. A light emitting device comprising:

10 a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element; and

a second transistor provided in said pixel for determining a light emission or non-emission of the light emitting element according to a video signal,

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wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and the first transistor is a depletion mode transistor.

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7. A device according to claim 6, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a

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threshold potential of the second transistor.

8. A device according to claim 6, wherein each of the first transistor and the second transistor has an N-type conductivity and
5 a threshold potential of the first transistor is lower than a threshold potential of the second transistor.

9. A device according to claim 6, wherein a channel length of the first transistor is longer than its channel width, and a channel
10 length of the second transistor is equal to or shorter than its channel width.

10. A device according to claim 9, a ratio of the channel length to the channel width of the first transistor is five or more.

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11. A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element; and

20 a second transistor provided in said pixel for determining a light emission or non-emission of the light emitting element according to a video signal; and

a third transistor provided in said pixel for controlling input of said video signal,

25 wherein the light emitting element is connected in series to

the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to the first power supply; and

5 the first transistor is a depletion mode transistor.

12. A device according to claim 11, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a
10 threshold potential of the second transistor.

13. A device according to claim 11, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold
15 potential of the second transistor.

14. A device according to claim 11, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel
20 width.

15. A device according to claim 14, a ratio of the channel length to the channel width of the first transistor is five or more.

25 16. A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element;

a second transistor provided in said pixel for determining a light emission or non-emission of the light emitting element according to a video signal; and

a third transistor provided in said pixel for controlling input of said video signal,

wherein

the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and

the first transistor is a depletion mode transistor.

17. A device according to claim 16, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.

18. A device according to claim 16, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.

19. A device according to claim 16, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.

20. A device according to claim 19, a ratio of the channel length to the channel width of the first transistor is five or more.

21. A light emitting device comprising:

a light emitting element provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the light emitting element;

a second transistor provided in said pixel for determining a light emission or non-emission of the light emitting element according to a video signal;

a third transistor provided in said pixel for controlling an input of the video signal; and

a fourth transistor provided in said pixel for setting the light emitting element in a non-emission state regardless of the video signal,

wherein the light emitting element is connected in series to the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to the

first power supply; and

the first transistor is a depletion mode transistor.

22. A device according to claim 21, wherein each of the first
5 transistor and the second transistor has a P-type conductivity and
a threshold potential of the first transistor is higher than a
threshold potential of the second transistor.

23. A device according to claim 21, wherein each of the first
10 transistor and the second transistor has an N-type conductivity and
a threshold potential of the first transistor is lower than a threshold
potential of the second transistor.

24. A device according to claim 21, wherein a channel length
15 of the first transistor is longer than its channel width, and a channel
length of the second transistor is equal to or shorter than its channel
width.

25. A device according to claim 24, a ratio of the channel length
20 to the channel width of the first transistor is five or more.

26. A light emitting device comprising a pixel comprising:
a light emitting element provided in a pixel;
a first transistor provided in said pixel for determining a
25 current value flowing in the light emitting element;

a second transistor provided in said pixel for determining a light emission or non-emission of the light emitting element according to a video signal;

a third transistor provided in said pixel for controlling an
5 input of the video signal; and

a fourth transistor provided in said pixel for setting the light emitting element in a non-emission state regardless of the video signal,

wherein the light emitting element is connected in series to
10 the first transistor and the second transistor between a first power supply and a second power supply;

a gate electrode of the first transistor is connected to either a source electrode or a drain electrode of the first transistor; and

the first transistor is a depletion mode transistor.

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27. A device according to claim 26, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.

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28. A device according to claim 26, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold potential of the second transistor.

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29. A device according to claim 26, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel width.

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30. A device according to claim 29, a ratio of the channel length to the channel width of the first transistor is five or more.

31. An element substrate comprising:

10 a pixel electrode provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the pixel electrode; and

a second transistor provided in said pixel for determining a current supply or no current supply to the pixel electrode according to a video signal,

wherein the first transistor is connected in series to the second transistor between a first power supply and the pixel electrode;

a gate electrode of the first transistor is connected to the first power supply; and

20 the first transistor is a depletion mode transistor.

32. A substrate according to claim 31, wherein each of the first transistor and the second transistor has a P-type conductivity and a threshold potential of the first transistor is higher than a threshold potential of the second transistor.

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33. A substrate according to claim 31, wherein each of the first transistor and the second transistor has an N-type conductivity and a threshold potential of the first transistor is lower than a threshold
5 potential of the second transistor.

34. A substrate according to claim 31, wherein a channel length of the first transistor is longer than its channel width, and a channel length of the second transistor is equal to or shorter than its channel
10 width.

35. A substrate according to claim 34, wherein a ratio of the channel length to the channel width of the first transistor is five or more.

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36. An element substrate comprising:

a pixel electrode provided in a pixel;

a first transistor provided in said pixel for determining a current value flowing in the pixel electrode; and

20 a second transistor provided in said pixel for determining a current supply or no current supply to the pixel electrode according to a video signal,

wherein the first transistor is connected in series to the second transistor between a first power supply and the pixel electrode;

25 a gate electrode of the first transistor is connected to either

a source electrode or a drain electrode of the first transistor; and
the first transistor is a depletion mode transistor.

37. A substrate according to claim 36 , wherein each of the first
5 transistor and the second transistor has a P-type conductivity and
a threshold potential of the first transistor is higher than a
threshold potential of the second transistor.

38. A substrate according to claim 36, wherein each of the first
10 transistor and the second transistor has an N-type conductivity and
a threshold potential of the first transistor is lower than a threshold
potential of the second transistor.

39. A substrate according to claim 36, wherein a channel length
15 of the first transistor is longer than its channel width, and a channel
length of the second transistor is equal to or shorter than its channel
width.

40. A substrate according to claim 39, wherein a ratio of the
20 channel length to the channel width of the first transistor is five
or more.